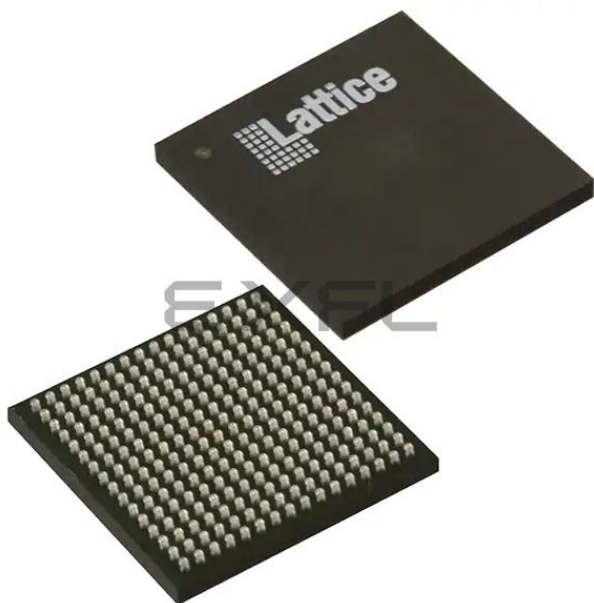




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	264
Number of Logic Elements/Cells	2112
Total RAM Bits	75776
Number of I/O	206
Number of Gates	-
Voltage - Supply	2.375V ~ 3.465V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LFBGA
Supplier Device Package	256-CABGA (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3l-2100c-6bg256c

Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In Ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/down counter with asynchronous clear
- Up/down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
 - A greater-than-or-equal-to B
 - A not-equal-to B
 - A less-than-or-equal-to B

Ripple mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per-slice basis to allow fast arithmetic functions to be constructed by concatenating slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed by using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals.

MachXO3L/LF devices support distributed memory initialization.

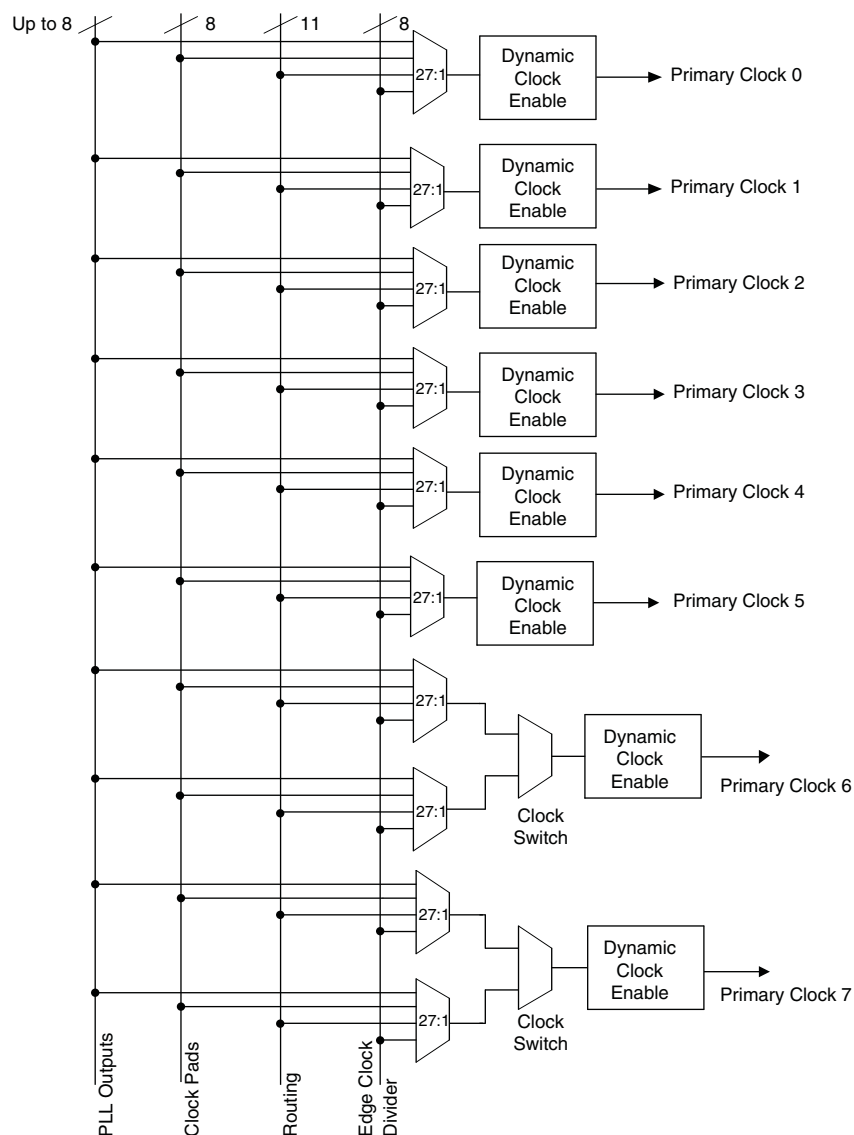
The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in MachXO3L/LF devices, please see TN1290, [Memory Usage Guide for MachXO3 Devices](#).

Table 2-3. Number of Slices Required For Implementing Distributed RAM

	SPR 16x4	PDPR 16x4
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

Figure 2-5. Primary Clocks for MachXO3L/LF Devices



Eight secondary high fanout nets are generated from eight 8:1 muxes as shown in Figure 2-6. One of the eight inputs to the secondary high fanout net input mux comes from dual function clock pins and the remaining seven come from internal routing. The maximum frequency for the secondary clock network is shown in MachXO3L/LF External Switching Characteristics table.

This phase shift can be either programmed during configuration or can be adjusted dynamically. In dynamic mode, the PLL may lose lock after a phase adjustment on the output used as the feedback source and not relock until the t_{LOCK} parameter has been satisfied.

The MachXO3L/LF also has a feature that allows the user to select between two different reference clock sources dynamically. This feature is implemented using the PLLREFCS primitive. The timing parameters for the PLL are shown in the [sysCLOCK PLL Timing](#) table.

The MachXO3L/LF PLL contains a WISHBONE port feature that allows the PLL settings, including divider values, to be dynamically changed from the user logic. When using this feature the EFB block must also be instantiated in the design to allow access to the WISHBONE ports. Similar to the dynamic phase adjustment, when PLL settings are updated through the WISHBONE port the PLL may lose lock and not relock until the t_{LOCK} parameter has been satisfied. The timing parameters for the PLL are shown in the [sysCLOCK PLL Timing](#) table.

For more details on the PLL and the WISHBONE interface, see TN1282, [MachXO3 sysCLOCK PLL Design and Usage Guide](#).

Figure 2-7. PLL Diagram

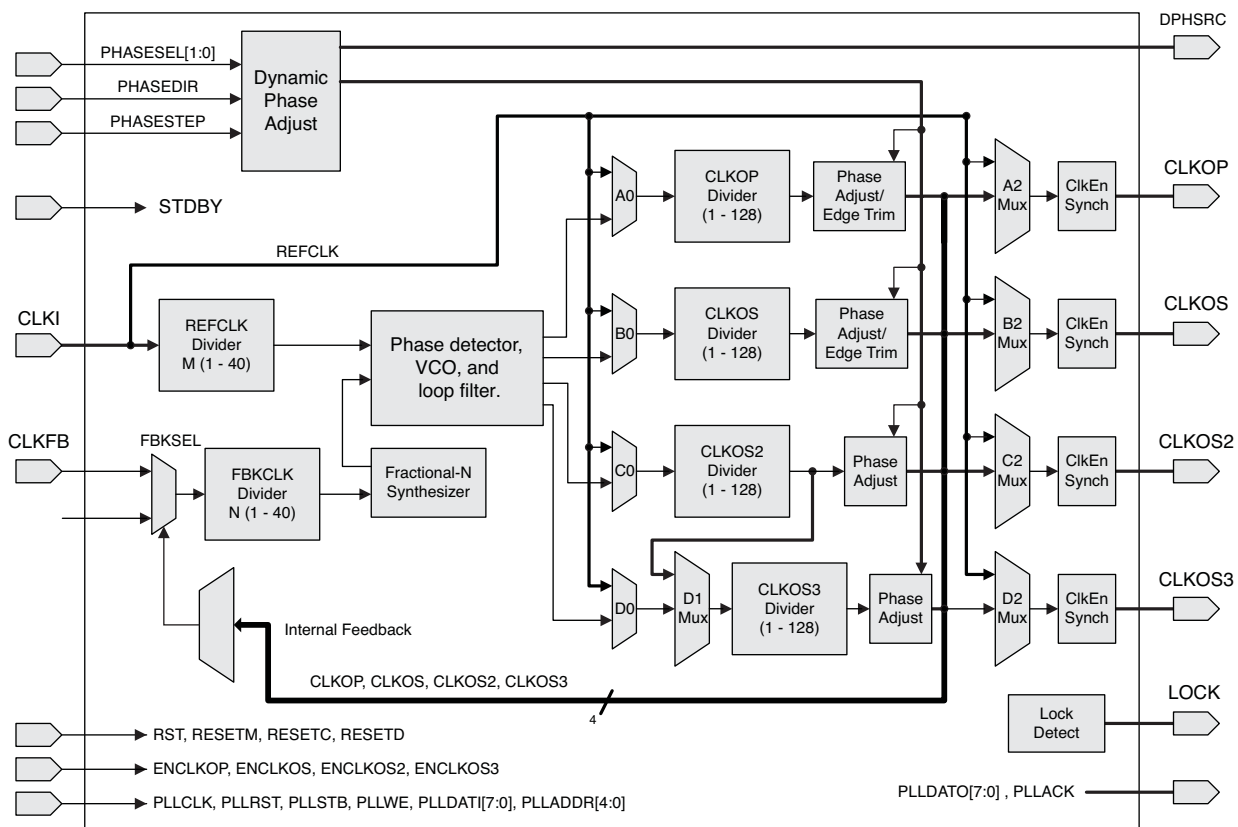


Table 2-4 provides signal descriptions of the PLL block.

Table 2-4. PLL Signal Descriptions

Port Name	I/O	Description
CLKI	I	Input clock to PLL
CLKFB	I	Feedback clock
PHASESEL[1:0]	I	Select which output is affected by Dynamic Phase adjustment ports
PHASEDIR	I	Dynamic Phase adjustment direction
PHASESTEP	I	Dynamic Phase step – toggle shifts VCO phase adjust by one step.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the NVCM or Configuration Flash.

MachXO3LF EBR initialization data can also be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO3LF devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.

Figure 2-11. Group of Four Programmable I/O Cells

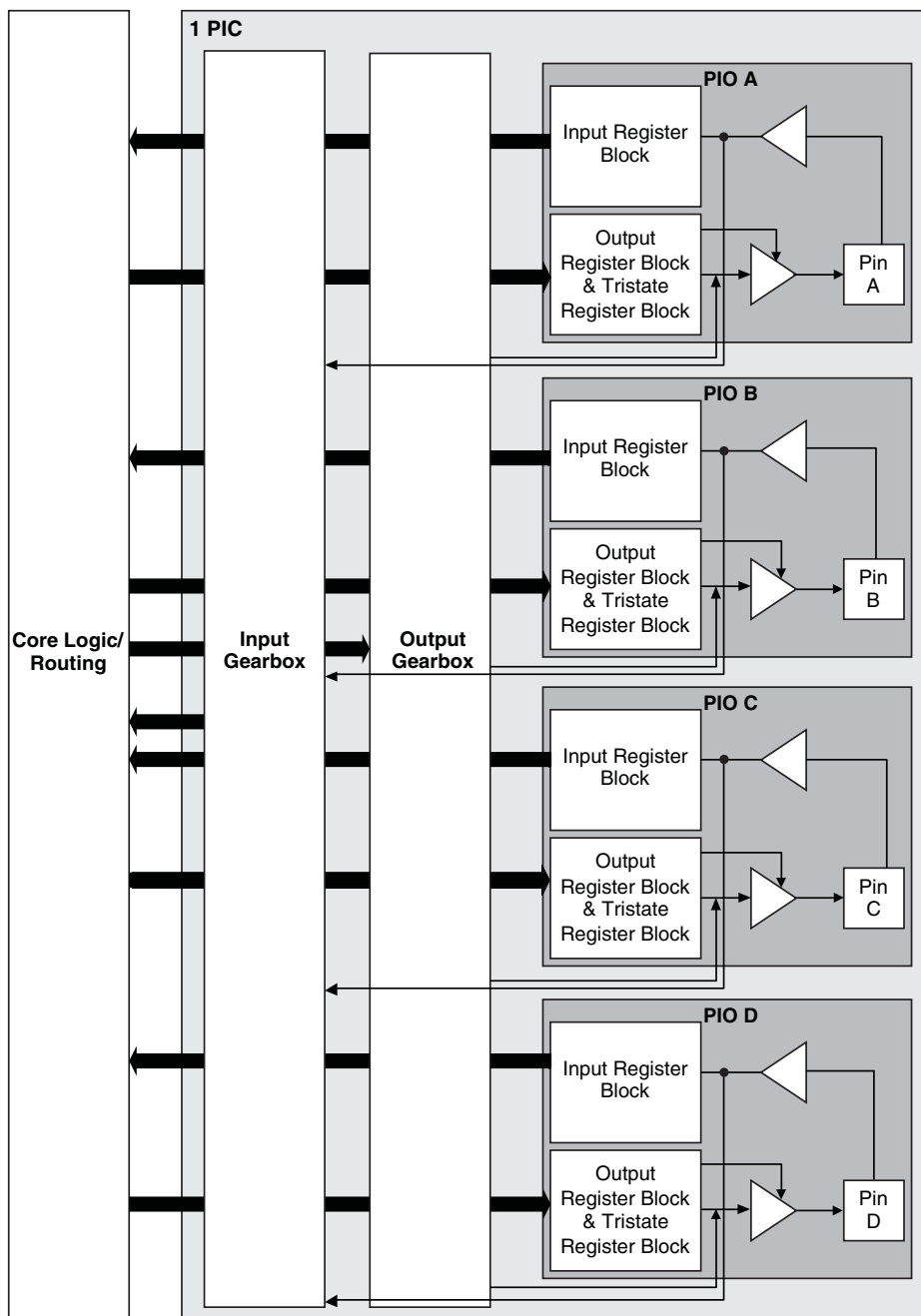


Table 2-12. Supported Output Standards

Output Standard	V _{CCIO} (Typ.)
Single-Ended Interfaces	
LVTTL	3.3
LVC MOS33	3.3
LVC MOS25	2.5
LVC MOS18	1.8
LVC MOS15	1.5
LVC MOS12	1.2
LVC MOS33, Open Drain	—
LVC MOS25, Open Drain	—
LVC MOS18, Open Drain	—
LVC MOS15, Open Drain	—
LVC MOS12, Open Drain	—
PCI33	3.3
Differential Interfaces	
LVDS ¹	2.5, 3.3
BLVDS, MLVDS, RSDS ¹	2.5
LVPECL ¹	3.3
MIPI ¹	2.5
LVTTL D	3.3
LVC MOS33D	3.3
LVC MOS25D	2.5
LVC MOS18D	1.8

1. These interfaces can be emulated with external resistors in all devices.

sysIO Buffer Banks

The numbers of banks vary between the devices of this family. MachXO3L/LF-1300 in the 256 Ball packages and the MachXO3L/LF-2100 and higher density devices have six I/O banks (one bank on the top, right and bottom side and three banks on the left side). The MachXO3L/LF-1300 and lower density devices have four banks (one bank per side). Figures 2-15 and 2-16 show the sysIO banks and their associated supplies for all devices.

For more details on these embedded functions, please refer to TN1293, [Using Hardened Control Functions in MachXO3 Devices](#).

User Flash Memory (UFM)

MachXO3LF devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I2C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1293, [Using Hardened Control Functions in MachXO3 Devices](#).

Standby Mode and Power Saving Options

MachXO3L/LF devices are available in two options, the C and E devices. The C devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the E devices operate at 1.2 V V_{CC} .

MachXO3L/LF devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO3L/LF devices support a low power Stand-by mode.

In the stand-by mode the MachXO3L/LF devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I²C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO3L/LF devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

Security and One-Time Programmable Mode (OTP)

For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM-based FPGAs. This is further enhanced by device locking. MachXO3L/LF devices contain security bits that, when set, prevent the readback of the SRAM configuration and NVCM/Flash spaces. The device can be in one of two modes:

1. Unlocked – Readback of the SRAM configuration and NVCM/Flash spaces is allowed.
2. Permanently Locked – The device is permanently locked.

Once set, the only way to clear the security bits is to erase the device. To further complement the security of the device, a One Time Programmable (OTP) mode is available. Once the device is set in this mode it is not possible to erase or re-program the NVCM/Flash and SRAM OTP portions of the device. For more details, refer to TN1279, [MachXO3 Programming and Configuration Usage Guide](#).

Password

The MachXO3LF supports a password-based security access feature also known as Flash Protect Key. Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. The Flash Protect Key feature provides a method of controlling access to the Configuration and Programming modes of the device. When enabled, the Configuration and Programming edit mode operations (including Write, Verify and Erase operations) are allowed only when coupled with a Flash Protect Key which matches that expected by the device. Without a valid Flash Protect Key, the user can perform only rudimentary non-configuration operations such as Read Device ID. For more details, refer to TN1313, [Using Password Security with MachXO3 Devices](#).

Dual Boot

MachXO3L/LF devices can optionally boot from two patterns, a primary bitstream and a golden bitstream. If the primary bitstream is found to be corrupt while being downloaded into the SRAM, the device shall then automatically re-boot from the golden bitstream. Note that the primary bitstream must reside in the external SPI Flash. The golden image MUST reside in an on-chip NVCM/Flash. For more details, refer to TN1279, [MachXO3 Programming and Configuration Usage Guide](#).

Soft Error Detection

The SED feature is a CRC check of the SRAM cells after the device is configured. This check ensures that the SRAM cells were configured successfully. This feature is enabled by a configuration bit option. The Soft Error Detection can also be initiated in user mode via an input to the fabric. The clock for the Soft Error Detection circuit is generated using a dedicated divider. The undivided clock from the on-chip oscillator is the input to this divider. For low power applications users can switch off the Soft Error Detection circuit. For more details, refer to TN1292, [MachXO3 Soft Error Detection Usage Guide](#).

Soft Error Correction

The MachXO3LF device supports Soft Error Correction (SEC). Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. When BACKGROUND_RECONFIG is enabled using the Lattice Diamond Software in a design, asserting the PROGRAMN pin or issuing the REFRESH sysConfig command refreshes the SRAM array from configuration memory. Only the detected error bit is corrected. No other SRAM cells are changed, allowing the user design to function uninterrupted.

During the project design phase, if the overall system cannot guarantee containment of the error or its subsequent effects on downstream data or control paths, Lattice recommends using SED only. The MachXO3 can then be soft-reset by asserting PROGRAMN or issuing the Refresh command over a sysConfig port in response to SED. Soft-reset additionally erases the SRAM array prior to the SRAM refresh, and asserts internal Reset circuitry to guarantee a known state. For more details, refer to TN1292, [MachXO3 Soft Error Detection \(SED\)/Correction \(SEC\) Usage Guide](#).

Power-On-Reset Voltage Levels^{1, 2, 3, 4, 5}

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for C devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Hot Socketing Specifications^{1, 2, 3}

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	μA

1. Insensitive to sequence of V_{CC} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO} .
2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).
3. I_{DK} is additive to I_{PU} , I_{PD} or I_{BH} .

ESD Performance

Please refer to the [MachXO2 Product Family Qualification Summary](#) for complete qualification data, including ESD performance.

Static Supply Current – C/E Devices^{1, 2, 3, 6}

Symbol	Parameter	Device	Typ. ⁴	Units
I_{CC}	Core Power Supply	LCMXO3L/LF-1300C 256 Ball Package	4.8	mA
		LCMXO3L/LF-2100C	4.8	mA
		LCMXO3L/LF-2100C 324 Ball Package	8.45	mA
		LCMXO3L/LF-4300C	8.45	mA
		LCMXO3L/LF-4300C 400 Ball Package	12.87	mA
		LCMXO3L/LF-6900C ⁷	12.87	mA
		LCMXO3L/LF-9400C ⁷	17.86	mA
		LCMXO3L/LF-640E	1.00	mA
		LCMXO3L/LF-1300E	1.00	mA
		LCMXO3L/LF-1300E 256 Ball Package	1.39	mA
		LCMXO3L/LF-2100E	1.39	mA
		LCMXO3L/LF-2100E 324 Ball Package	2.55	mA
		LCMXO3L/LF-4300E	2.55	mA
		LCMXO3L/LF-6900E	4.06	mA
		LCMXO3L/LF-9400E	5.66	mA
I_{CCIO}	Bank Power Supply ⁵ VCCIO = 2.5 V	All devices	0	mA

1. For further information on supply current, please refer to TN1289, [Power Estimation and Management for MachXO3 Devices](#).
2. Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip oscillator is off, on-chip PLL is off.
3. Frequency = 0 MHz.
4. $T_J = 25^\circ\text{C}$, power supplies at nominal voltage.
5. Does not include pull-up/pull-down.
6. To determine the MachXO3L/LF peak start-up current data, use the Power Calculator tool.
7. Determination of safe ambient operating conditions requires use of the Diamond Power Calculator tool.

sysIO Single-Ended DC Electrical Characteristics^{1, 2}

Input/Output Standard	V _{IL}		V _{IH}		V _{OL} Max. (V)	V _{OH} Min. (V)	I _{OL} Max. ⁴ (mA)	I _{OH} Max. ⁴ (mA)
	Min. (V) ³	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	V _{CCIO} - 0.4	4	-4
							8	-8
							12	-12
							16	-16
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	V _{CCIO} - 0.4	0.1	-0.1
							4	-4
							8	-8
							12	-12
LVCMOS 1.8	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	0.1	-0.1
							4	-4
							8	-8
							12	-12
LVCMOS 1.5	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	0.1	-0.1
							4	-4
							8	-8
							12	-12
LVCMOS 1.2	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	0.1	-0.1
							4	-2
							8	-6
							12	-12
LVCMOS25R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R25	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R25	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS12R33	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS10R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain

1. MachXO3L/LF devices allow LVCMOS inputs to be placed in I/O banks where V_{CCIO} is different from what is specified in the applicable JEDEC specification. This is referred to as a ratioed input buffer. In a majority of cases this operation follows or exceeds the applicable JEDEC specification. The cases where MachXO3L/LF devices do not meet the relevant JEDEC specification are documented in the table below.
2. MachXO3L/LF devices allow for LVCMOS referenced I/Os which follow applicable JEDEC specifications. For more details about mixed mode operation please refer to please refer to TN1280, [MachXO3 sysIO Usage Guide](#).
3. The dual function I²C pins SCL and SDA are limited to a V_{IL} min of -0.25 V or to -0.3 V with a duration of <10 ns.
4. For electromigration, the average DC current sourced or sinked by I/O pads between two consecutive V_{CCIO} or GND pad connections, or between the last V_{CCIO} or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed a maximum of n * 8 mA. "n" is the number of I/O pads between the two consecutive bank V_{CCIO} or GND connections or between the last V_{CCIO} and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

sysIO Differential Electrical Characteristics

The LVDS differential output buffers are available on the top side of the MachXO3L/LF PLD family.

LVDS

Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Typ.	Max.	Units
V_{INP} V_{INM}	Input Voltage	$V_{CCIO} = 3.3 \text{ V}$	0	—	2.605	V
		$V_{CCIO} = 2.5 \text{ V}$	0	—	2.05	V
V_{THD}	Differential Input Threshold		± 100	—		mV
V_{CM}	Input Common Mode Voltage	$V_{CCIO} = 3.3 \text{ V}$	0.05	—	2.6	V
		$V_{CCIO} = 2.5 \text{ V}$	0.05	—	2.0	V
I_{IN}	Input current	Power on	—	—	± 10	μA
V_{OH}	Output high voltage for V_{OP} or V_{OM}	$R_T = 100 \text{ Ohm}$	—	1.375	—	V
V_{OL}	Output low voltage for V_{OP} or V_{OM}	$R_T = 100 \text{ Ohm}$	0.90	1.025	—	V
V_{OD}	Output voltage differential	$(V_{OP} - V_{OM})$, $R_T = 100 \text{ Ohm}$	250	350	450	mV
ΔV_{OD}	Change in V_{OD} between high and low		—	—	50	mV
V_{OS}	Output voltage offset	$(V_{OP} - V_{OM})/2$, $R_T = 100 \text{ Ohm}$	1.125	1.20	1.395	V
ΔV_{OS}	Change in V_{OS} between H and L		—	—	50	mV
I_{OSD}	Output short circuit current	$V_{OD} = 0 \text{ V}$ driver outputs shorted	—	—	24	mA

MIPI D-PHY Emulation

MachXO3L/LF devices can support MIPI D-PHY unidirectional HS (High Speed) and bidirectional LP (Low Power) inputs and outputs via emulation. In conjunction with external resistors High Speed IOs use the LVDS25E buffer and Low Power IOs use the LVC MOS buffers. The scheme shown in Figure 3-4 is one possible solution for MIPI D-PHY Receiver implementation. The scheme shown in Figure 3-5 is one possible solution for MIPI D-PHY Transmitter implementation.

Figure 3-4. MIPI D-PHY Input Using External Resistors

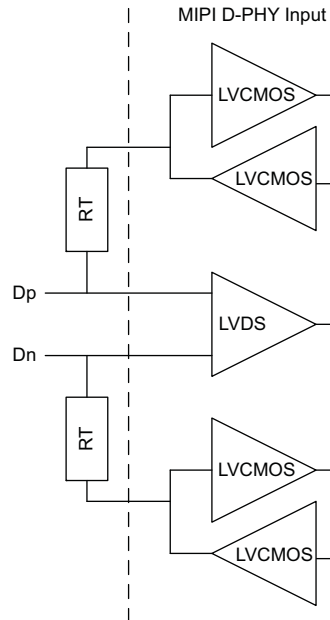


Table 3-4. MIPI DC Conditions¹

	Description	Min.	Typ.	Max.	Units
Receiver					
External Termination					
RT	1% external resistor with VCCIO=2.5 V	—	50	—	Ohms
	1% external resistor with VCCIO=3.3 V	—	50	—	Ohms
High Speed					
VCCIO	VCCIO of the Bank with LVDS Emulated input buffer	—	2.5	—	V
	VCCIO of the Bank with LVDS Emulated input buffer	—	3.3	—	V
VCMRX	Common-mode voltage HS receive mode	150	200	250	mV
WIDTH	Differential input high threshold	—	—	100	mV
VIDTL	Differential input low threshold	-100	—	—	mV
VIHHS	Single-ended input high voltage	—	—	300	mV
VILHS	Single-ended input low voltage	100	—	—	mV
ZID	Differential input impedance	80	100	120	Ohms

Parameter	Description	Device	-6		-5		Units
			Min.	Max.	Min.	Max.	
Generic DDRX1 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_RX.SCLK.Aligned ^{8,9}							
t _{DVA}	Input Data Valid After CLK	All MachXO3L/LF devices, all sides	—	0.317	—	0.344	UI
t _{DVE}	Input Data Hold After CLK		0.742	—	0.702	—	UI
f _{DATA}	DDRX1 Input Data Speed		—	300	—	250	Mbps
f _{DDRX1}	DDRX1 SCLK Frequency		—	150	—	125	MHz
Generic DDRX1 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_RX.SCLK.Centered ^{8,9}							
t _{SU}	Input Data Setup Before CLK	All MachXO3L/LF devices, all sides	0.566	—	0.560	—	ns
t _{HO}	Input Data Hold After CLK		0.778	—	0.879	—	ns
f _{DATA}	DDRX1 Input Data Speed		—	300	—		Mbps
f _{DDRX1}	DDRX1 SCLK Frequency		—	150	—	125	MHz
Generic DDRX2 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_RX.ECLK.Aligned ^{8,9}							
t _{DVA}	Input Data Valid After CLK	MachXO3L/LF devices, bottom side only	—	0.316	—	0.342	UI
t _{DVE}	Input Data Hold After CLK		0.710	—	0.675	—	UI
f _{DATA}	DDRX2 Serial Input Data Speed		—	664	—	554	Mbps
f _{DDRX2}	DDRX2 ECLK Frequency		—	332	—	277	MHz
f _{SCLK}	SCLK Frequency		—	166	—	139	MHz
Generic DDRX2 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX2_RX.ECLK.Centered ^{8,9}							
t _{SU}	Input Data Setup Before CLK	MachXO3L/LF devices, bottom side only	0.233	—	0.219	—	ns
t _{HO}	Input Data Hold After CLK		0.287	—	0.287	—	ns
f _{DATA}	DDRX2 Serial Input Data Speed		—	664	—	554	Mbps
f _{DDRX2}	DDRX2 ECLK Frequency		—	332	—	277	MHz
f _{SCLK}	SCLK Frequency		—	166	—	139	MHz
Generic DDR4 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Aligned ⁸							
t _{DVA}	Input Data Valid After ECLK	MachXO3L/LF devices, bottom side only	—	0.307	—	0.320	UI
t _{DVE}	Input Data Hold After ECLK		0.782	—	0.699	—	UI
f _{DATA}	DDRX4 Serial Input Data Speed		—	800	—	630	Mbps
f _{DDRX4}	DDRX4 ECLK Frequency		—	400	—	315	MHz
f _{SCLK}	SCLK Frequency		—	100	—	79	MHz
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Centered ⁸							
t _{SU}	Input Data Setup Before ECLK	MachXO3L/LF devices, bottom side only	0.233	—	0.219	—	ns
t _{HO}	Input Data Hold After ECLK		0.287	—	0.287	—	ns
f _{DATA}	DDRX4 Serial Input Data Speed		—	800	—	630	Mbps
f _{DDRX4}	DDRX4 ECLK Frequency		—	400	—	315	MHz
f _{SCLK}	SCLK Frequency		—	100	—	79	MHz
7:1 LVDS Inputs (GDDR71_RX.ECLK.7:1) ⁹							
t _{DVA}	Input Data Valid After ECLK	MachXO3L/LF devices, bottom side only	—	0.290	—	0.320	UI
t _{DVE}	Input Data Hold After ECLK		0.739	—	0.699	—	UI
f _{DATA}	DDR71 Serial Input Data Speed		—	756	—	630	Mbps
f _{DDR71}	DDR71 ECLK Frequency		—	378	—	315	MHz
f _{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	108	—	90	MHz

sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Min.	Max.	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)		7	400	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS, CLKOS2)		1.5625	400	MHz
f_{OUT2}	Output Frequency (CLKOS3 cascaded from CLKOS2)		0.0122	400	MHz
f_{VCO}	PLL VCO Frequency		200	800	MHz
f_{PFD}	Phase Detector Input Frequency		7	400	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	Without duty trim selected ³	45	55	%
$t_{DT_TRIM}^7$	Edge Duty Trim Accuracy		-75	75	%
t_{PH}^4	Output Phase Accuracy		-6	6	%
$t_{OPJIT}^{1,8}$	Output Clock Period Jitter	$f_{OUT} > 100$ MHz	—	150	ps p-p
		$f_{OUT} < 100$ MHz	—	0.007	UIPP
	Output Clock Cycle-to-cycle Jitter	$f_{OUT} > 100$ MHz	—	180	ps p-p
		$f_{OUT} < 100$ MHz	—	0.009	UIPP
	Output Clock Phase Jitter	$f_{PFD} > 100$ MHz	—	160	ps p-p
		$f_{PFD} < 100$ MHz	—	0.011	UIPP
	Output Clock Period Jitter (Fractional-N)	$f_{OUT} > 100$ MHz	—	230	ps p-p
		$f_{OUT} < 100$ MHz	—	0.12	UIPP
	Output Clock Cycle-to-cycle Jitter (Fractional-N)	$f_{OUT} > 100$ MHz	—	230	ps p-p
		$f_{OUT} < 100$ MHz	—	0.12	UIPP
t_{SPO}	Static Phase Offset	Divider ratio = integer	-120	120	ps
t_W	Output Clock Pulse Width	At 90% or 10% ³	0.9	—	ns
$t_{LOCK}^{2,5}$	PLL Lock-in Time		—	15	ms
t_{UNLOCK}	PLL Unlock Time		—	50	ns
t_{IPJIT}^6	Input Clock Period Jitter	$f_{PFD} \geq 20$ MHz	—	1,000	ps p-p
		$f_{PFD} < 20$ MHz	—	0.02	UIPP
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{STABLE}^5	STANDBY High to PLL Stable		—	15	ms
t_{RST}	RST/RESETM Pulse Width		1	—	ns
t_{RSTREC}	RST Recovery Time		1	—	ns
t_{RST_DIV}	RESETC/D Pulse Width		10	—	ns
t_{RSTREC_DIV}	RESETC/D Recovery Time		1	—	ns
t_{ROTATE_SETUP}	PHASESTEP Setup Time		10	—	ns
t_{ROTATE_WD}	PHASESTEP Pulse Width		4	—	VCO Cycles

1. Period jitter sample is taken over 10,000 samples of the primary PLL output with a clean reference clock. Cycle-to-cycle jitter is taken over 1000 cycles. Phase jitter is taken over 2000 cycles. All values per JESD65B.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Using LVDS output buffers.
4. CLKOS as compared to CLKOP output for one phase step at the maximum VCO frequency. See TN1282, [MachXO3 sysCLOCK PLL Design and Usage Guide](#) for more details.
5. At minimum f_{PFD} . As the f_{PFD} increases the time will decrease to approximately 60% the value listed.
6. Maximum allowed jitter on an input clock. PLL unlock may occur if the input jitter exceeds this specification. Jitter on the input clock may be transferred to the output clocks, resulting in jitter measurements outside the output specifications listed in this table.
7. Edge Duty Trim Accuracy is a percentage of the setting value. Settings available are 70 ps, 140 ps, and 280 ps in addition to the default value of none.
8. Jitter values measured with the internal oscillator operating. The jitter values will increase with loading of the PLD fabric and in the presence of SSO noise.

	MachXO3L/LF-6900				
	CSFBGA256	CSFBGA324	CABGA256	CABGA324	CABGA400
General Purpose IO per Bank					
Bank 0	50	73	50	71	83
Bank 1	52	68	52	68	84
Bank 2	52	72	52	72	84
Bank 3	16	24	16	24	28
Bank 4	16	16	16	16	24
Bank 5	20	28	20	28	32
Total General Purpose Single Ended IO	206	281	206	279	335
Differential IO per Bank					
Bank 0	25	36	25	36	42
Bank 1	26	34	26	34	42
Bank 2	26	36	26	36	42
Bank 3	8	12	8	12	14
Bank 4	8	8	8	8	12
Bank 5	10	14	10	14	16
Total General Purpose Differential IO	103	140	103	140	168
Dual Function IO	37	37	37	37	37
Number 7:1 or 8:1 Gearboxes					
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	20	21	20	21	21
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	20	21	20	21	21
High-speed Differential Outputs					
Bank 0	20	21	20	21	21
VCCIO Pins					
Bank 0	4	4	4	4	5
Bank 1	3	4	4	4	5
Bank 2	4	4	4	4	5
Bank 3	2	2	1	2	2
Bank 4	2	2	2	2	2
Bank 5	2	2	1	2	2
VCC	8	8	8	10	10
GND	24	16	24	16	33
NC	0	0	1	0	0
Reserved for Configuration	1	1	1	1	1
Total Count of Bonded Pins	256	324	256	324	400

MachXO3L Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-640E-5MG121C	640	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3L-640E-6MG121C	640	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3L-640E-5MG121I	640	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3L-640E-6MG121I	640	1.2 V	6	Halogen-Free csfBGA	121	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-1300E-5UWG36CTR	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3L-1300E-5UWG36CTR50	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3L-1300E-5UWG36CTR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3L-1300E-5UWG36ITR	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3L-1300E-5UWG36ITR50	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3L-1300E-5UWG36ITR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3L-1300E-5MG121C	1300	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3L-1300E-6MG121C	1300	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3L-1300E-5MG121I	1300	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3L-1300E-6MG121I	1300	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3L-1300E-5MG256C	1300	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-1300E-6MG256C	1300	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-1300E-5MG256I	1300	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-1300E-6MG256I	1300	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-1300C-5BG256C	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-1300C-6BG256C	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-1300C-5BG256I	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-1300C-6BG256I	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-2100E-5UWG49CTR	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3L-2100E-5UWG49CTR50	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3L-2100E-5UWG49CTR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3L-2100E-5UWG49ITR	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3L-2100E-5UWG49ITR50	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3L-2100E-5UWG49ITR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3L-2100E-5MG121C	2100	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3L-2100E-6MG121C	2100	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3L-2100E-5MG121I	2100	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3L-2100E-6MG121I	2100	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3L-2100E-5MG256C	2100	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-2100E-6MG256C	2100	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-2100E-5MG256I	2100	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-2100E-6MG256I	2100	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-2100E-5MG324C	2100	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3L-2100E-6MG324C	2100	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3L-2100E-5MG324I	2100	1.2 V	5	Halogen-Free csfBGA	324	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-2100E-6MG324I	2100	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3L-2100C-5BG256C	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-2100C-6BG256C	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-2100C-5BG256I	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-2100C-6BG256I	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3L-2100C-5BG324C	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3L-2100C-6BG324C	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3L-2100C-5BG324I	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3L-2100C-6BG324I	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-4300E-5UWG81CTR	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3L-4300E-5UWG81CTR50	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3L-4300E-5UWG81CTR1K	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3L-4300E-5UWG81ITR	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3L-4300E-5UWG81ITR50	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3L-4300E-5UWG81ITR1K	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3L-4300E-5MG121C	4300	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3L-4300E-6MG121C	4300	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3L-4300E-5MG121I	4300	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3L-4300E-6MG121I	4300	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3L-4300E-5MG256C	4300	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-4300E-6MG256C	4300	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-4300E-5MG256I	4300	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-4300E-6MG256I	4300	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-4300E-5MG324C	4300	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3L-4300E-6MG324C	4300	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3L-4300E-5MG324I	4300	1.2 V	5	Halogen-Free csfBGA	324	IND
LCMXO3L-4300E-6MG324I	4300	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3L-4300C-5BG256C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-4300C-6BG256C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-4300C-5BG256I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-4300C-6BG256I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3L-4300C-5BG324C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3L-4300C-6BG324C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3L-4300C-5BG324I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3L-4300C-6BG324I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND
LCMXO3L-4300C-5BG400C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3L-4300C-6BG400C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3L-4300C-5BG400I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3L-4300C-6BG400I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-6900E-5MG256C	6900	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-6900E-6MG256C	6900	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-6900E-5MG256I	6900	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-6900E-6MG256I	6900	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-6900E-5MG324C	6900	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3L-6900E-6MG324C	6900	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3L-6900E-5MG324I	6900	1.2 V	5	Halogen-Free csfBGA	324	IND
LCMXO3L-6900E-6MG324I	6900	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3L-6900C-5BG256C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-6900C-6BG256C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-6900C-5BG256I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-6900C-6BG256I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3L-6900C-5BG324C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3L-6900C-6BG324C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3L-6900C-5BG324I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3L-6900C-6BG324I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND
LCMXO3L-6900C-5BG400C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3L-6900C-6BG400C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3L-6900C-5BG400I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3L-6900C-6BG400I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-9400E-5MG256C	9400	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-9400E-6MG256C	9400	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-9400E-5MG256I	9400	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-9400E-6MG256I	9400	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-9400C-5BG256C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-9400C-6BG256C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-9400C-5BG256I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-9400C-6BG256I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3L-9400C-5BG400C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3L-9400C-6BG400C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3L-9400C-5BG400I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3L-9400C-6BG400I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	400	IND
LCMXO3L-9400C-5BG484C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	484	COM
LCMXO3L-9400C-6BG484C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	484	COM
LCMXO3L-9400C-5BG484I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	484	IND
LCMXO3L-9400C-6BG484I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	484	IND

Date	Version	Section	Change Summary
February 2017	1.8	Architecture	Updated Supported Standards section. Corrected “MDVS” to “MLDVS” in Table 2-11, Supported Input Standards.
		DC and Switching Characteristics	Updated ESD Performance section. Added reference to the MachXO2 Product Family Qualification Summary document.
			Updated Static Supply Current – C/E Devices section. Added footnote 7.
			Updated MachXO3L/LF External Switching Characteristics – C/E Devices section. — Populated values for MachXO3L/LF-9400. — Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, corrected “t _{DVB} ” to “t _{DIB} ” and “t _{DVA} ” to “t _{DIA} ” and revised their descriptions. — Added Figure 3-6, Receiver GDDR71_RX Waveforms and Figure 3-7, Transmitter GDDR71_TX Waveforms.
		Pinout Information	Updated the Pin Information Summary section. Added MachXO3L/LF-9600C packages.
May 2016	1.7	DC and Switching Characteristics	Updated Absolute Maximum Ratings section. Modified I/O Tri-state Voltage Applied and Dedicated Input Voltage Applied footnotes.
			Updated sysIO Recommended Operating Conditions section. — Added standards. — Added V _{REF} (V) — Added footnote 4.
			Updated sysIO Single-Ended DC Electrical Characteristics section. Added I/O standards.
		Ordering Information	Updated MachXO3L Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.
			Updated MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.